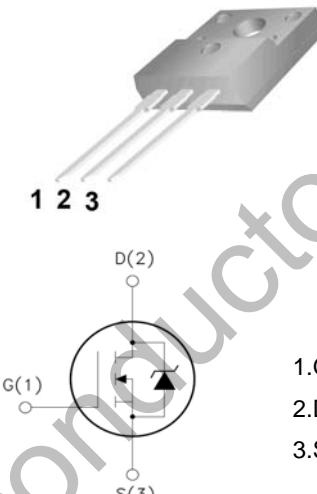


 <b>WGF6N70A</b>	<b>TO-220F</b>  <b>RoHS COMPLIANT</b>
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### Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain-Source Voltage	700	V
I <sub>D</sub>	Drain Current	T <sub>j</sub> =25°C	6.0
		T <sub>j</sub> =100°C	3.9
V <sub>GS(TH)</sub>	Gate Threshold Voltage	±30	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (note1)	300	mJ
I <sub>AR</sub>	Avalanche Current (note2)	6.0	A
P <sub>D</sub>	Power Dissipation (T <sub>j</sub> =25°C)	40	W
T <sub>j</sub>	Junction Temperature(Max)	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJC</sub>	Thermal Resistance,Junction to Case	-	3.12	°C/W
R <sub>θJA</sub>	Thermal Resistance,Junction to Ambient	-	62.5	°C/W

**Electrical Characteristics** (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250µA, V <sub>GS</sub> =0	700	-	-	V
△BV <sub>DSS</sub> /△T <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250µA, Reference to 25°C	-	0.6	-	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =700V, V <sub>GS</sub> =0V	-	-	1	µA
		V <sub>DS</sub> =560V, T <sub>j</sub> =125°C			10	
I <sub>GSSF</sub>	Gate-body leakage Current, Forward	V <sub>GS</sub> =+30V, V <sub>DS</sub> =0V	-	-	100	nA
I <sub>GSSR</sub>	Gate-body leakage Current, Reverse	V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V	-	-	-100	
<b>On Characteristics</b>						
V <sub>GS(TH)</sub>	Date Threshold Voltage	I <sub>D</sub> =250µA, V <sub>DS</sub> =V <sub>GS</sub>	2	-	4	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	I <sub>D</sub> =3A, V <sub>GS</sub> =10V	-	1.2	1.4	Ω
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0, f=1.0MHz	-	1100	-	pF
C <sub>oss</sub>	Output Capacitance		-	125	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	15	-	
<b>Switching Characteristics</b>						
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =350V, I <sub>D</sub> =6A R <sub>G</sub> =25Ω (Note 3,4)	-	13	35	ns
T <sub>r</sub>	Turn-On Rise Time		-	45	100	
T <sub>d(off)</sub>	Turn-Off Delay Time		-	25	60	
T <sub>f</sub>	Turn-Off Rise Time		-	35	80	
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =560V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A (Note 3,4)	-	30	40	nC
Q <sub>gs</sub>	Gate-Source Charge		-	3.5	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	6.5	-	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>s</sub>	Max. Diode Forward Current	-	-	-	6	A
I <sub>SM</sub>	Max. Pulsed Forward Current	-	-	-	24	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>D</sub> =6A	-	-	1.25	V
T <sub>rr</sub>	Reverse Recovery Time	I <sub>s</sub> =6A, V <sub>GS</sub> =0V diF/dt=100A/µs (Note 3)	-	310	-	nS
Q <sub>rr</sub>	Reverse Recovery Charge		-	2.1	-	µC

Notes : 1, L=27.5mH, IAS=6A, VDD=50V, RG=25Ω, Starting TJ =25°C

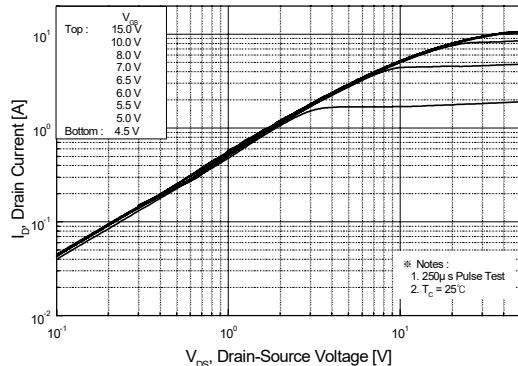
2, Repetitive Rating : Pulse width limited by maximum junction temperature

3, Pulse Test : Pulse Width ≤ 300µs, Duty Cycle ≤ 2%

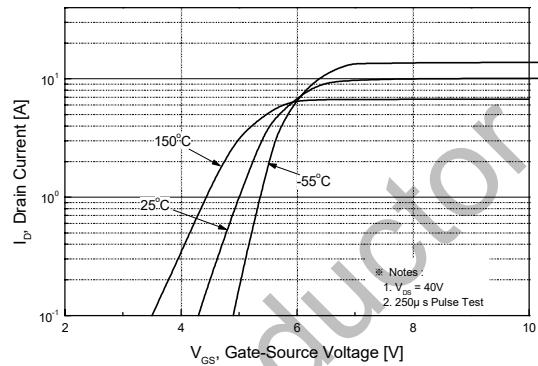
4, Essentially Independent of Operating Temperature

## Typical Characteristics

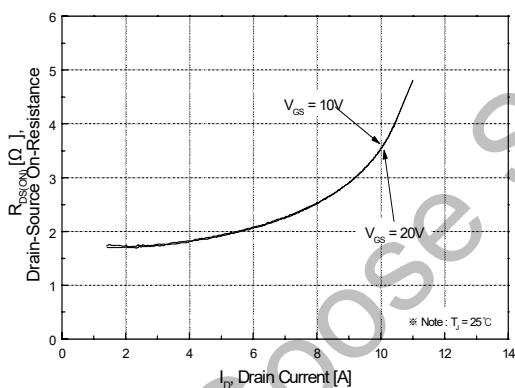
**Figure 1. On-Region Characteristics**



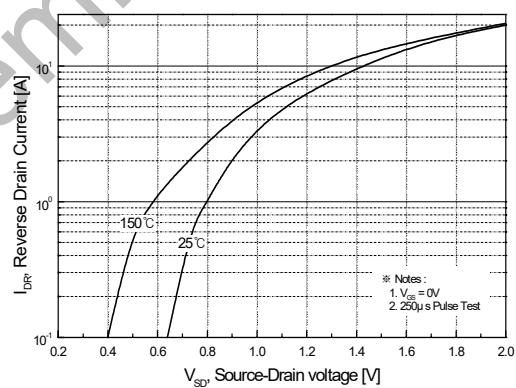
**Figure 2. Transfer Characteristics**



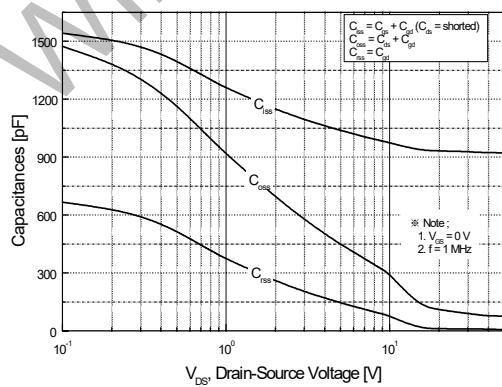
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



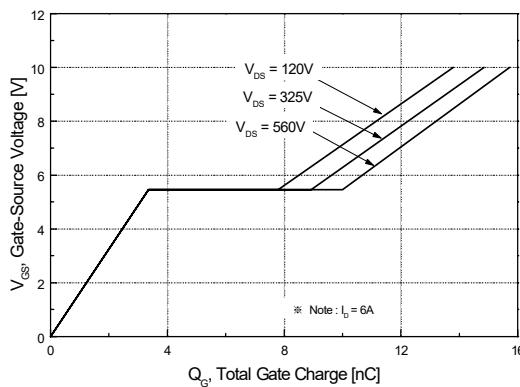
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

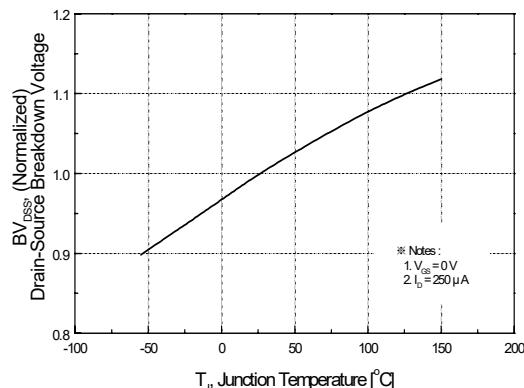
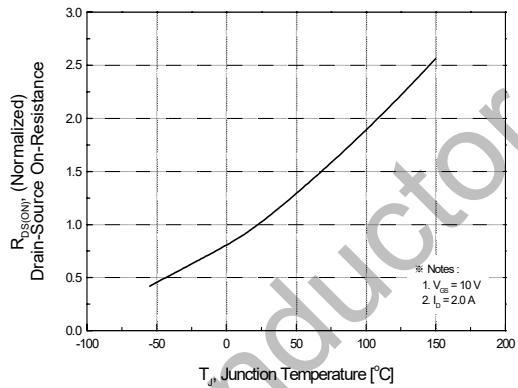
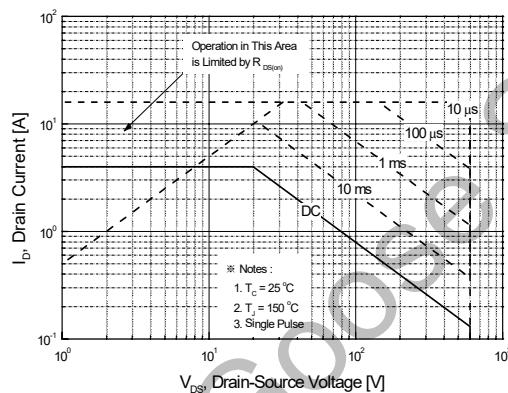
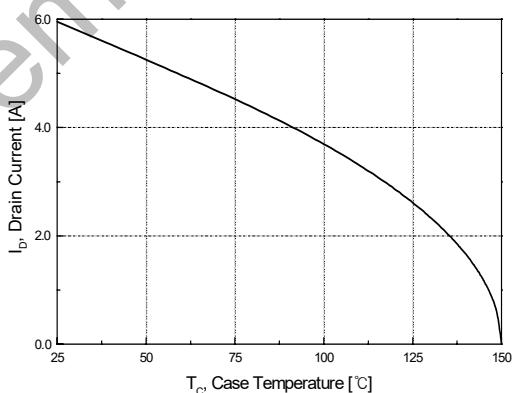
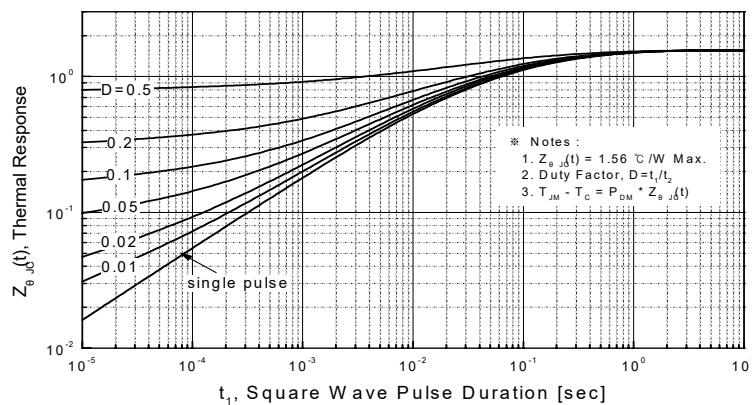


**Figure 5. Capacitance Characteristics**

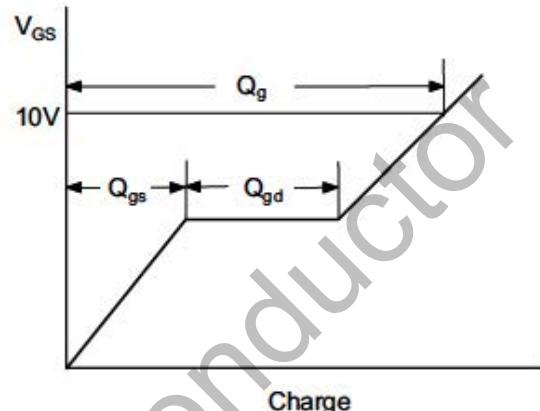
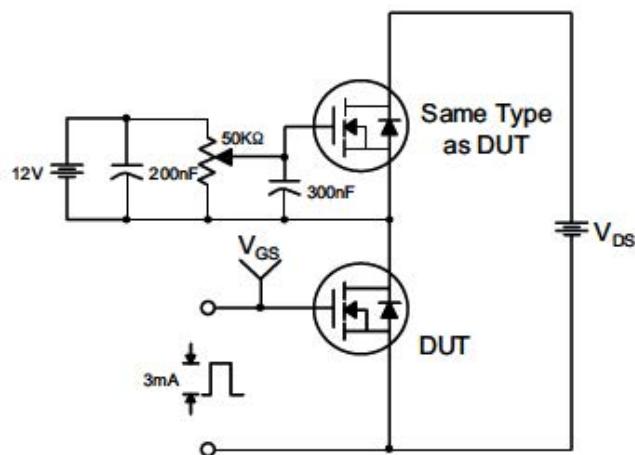


**Figure 6. Gate Charge Characteristics**

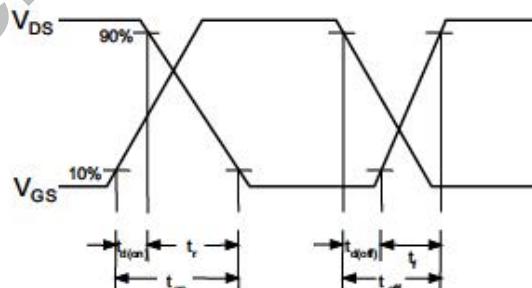
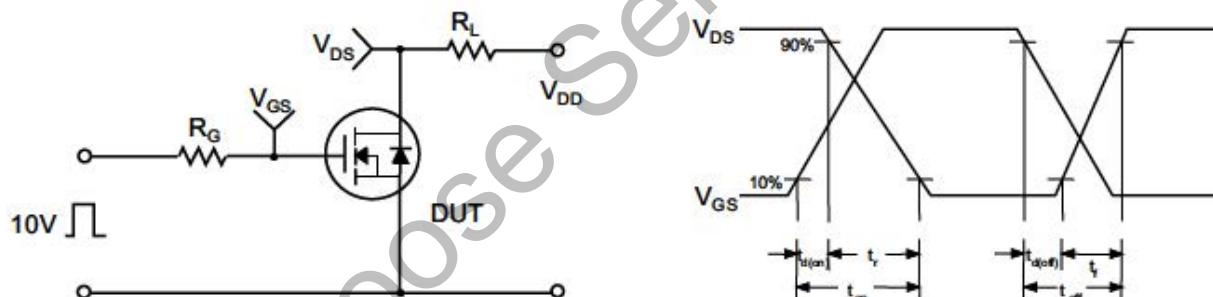


**Typical Characteristics (Continued)****Figure 7. Breakdown Voltage Variation vs. Temperature****Figure 8. On-Resistance Variation vs. Temperature****Figure 9. Maximum Safe Operating Area****Figure 10. Maximum Drain Current vs. Case Temperature****Figure 11. Transient Thermal Response Curve**

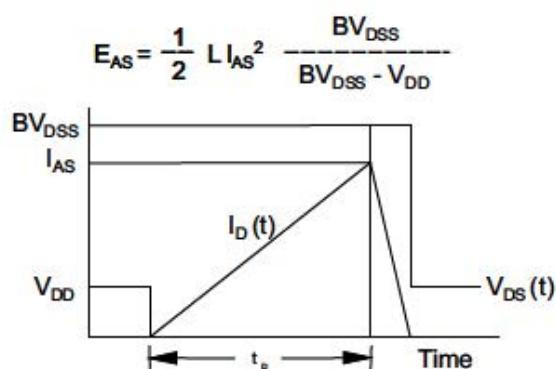
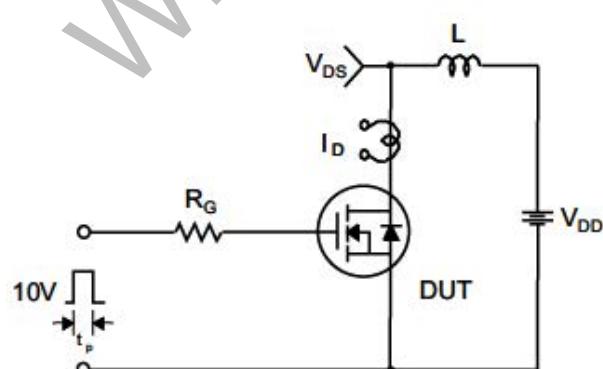
Gate Charge Test Circuit &amp; Waveform



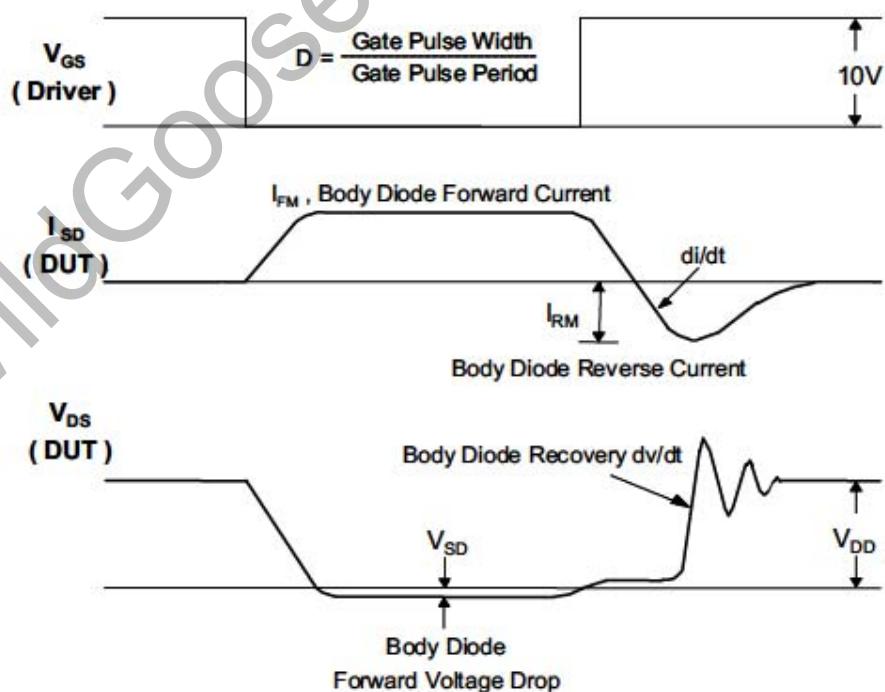
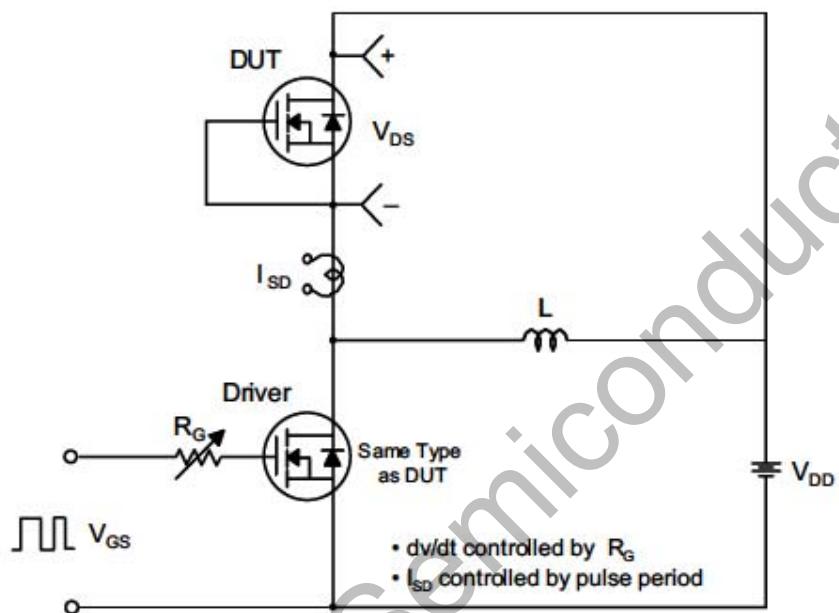
Resistive Switching Test Circuit &amp; Waveforms



Unclamped Inductive Switching Test Circuit &amp; Waveforms

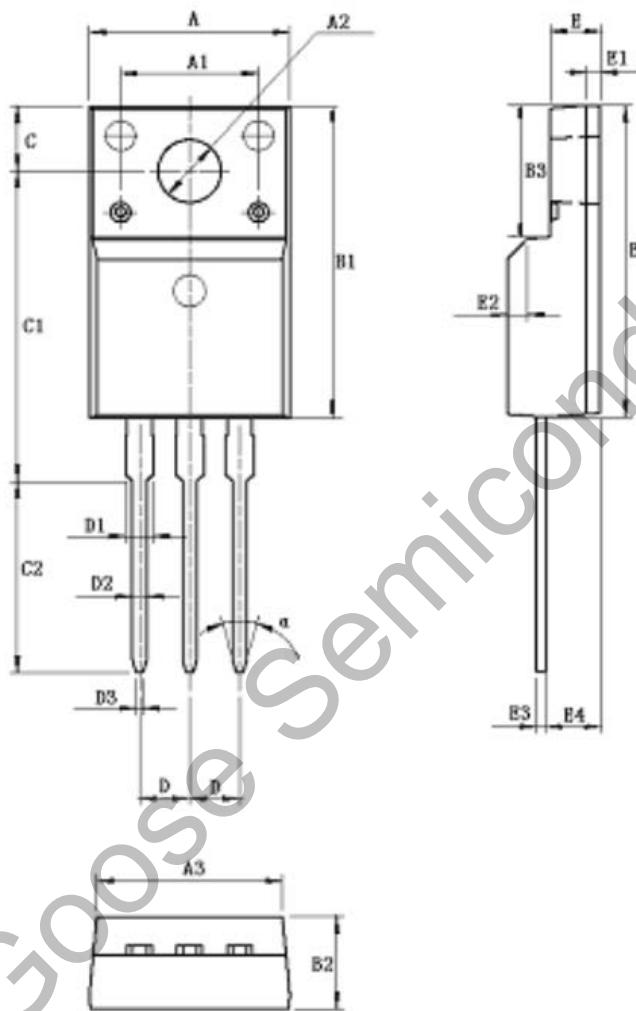


## Peak Diode Recovery dv/dt Test Circuit &amp; Waveforms



**Package Dimension**

TO-220F



单位: mm

Symbol	Min	Max	Symbol	Min	Max
A	9.96	10.36	D		2.54
A1		7.00	D1	1.15	1.35
A2	3.08	3.28	D2	0.70	0.90
A3	9.25	9.65	D3	0.28	0.48
B1	15.70	16.10	E	2.34	2.74
B2	4.50	4.90	E1		0.70
B3	6.20	6.80	E2		1.0×45°
C	3.20	3.40	E3	0.36	0.65
C1	15.20	16.00	E4	2.55	2.95
C2	9.75	10.15	a(度)		30°